Correction: ZnO nanorods decorated with metal sulfides as stable and efficient counter-electrode materials for high-efficiency quantum dot-sensitized solar cells

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There is an error in the film thicknesses of the ZnO/metal sulfides section of the above manuscript. The correct film thicknesses of the ZnO/metal sulfides are described below.

It is well known that the film thickness of FTO layer is 0.62 μm, which is in good agreement with the result obtained in Fig. 1(k). Based on these data, the ZnO/metal sulfide thicknesses were carefully calculated again by subtracting the thickness of FTO from the total FTO/ZnO/metal sulfide thicknesses. Based on this, the real film thicknesses are 1.47 μm for ZnO nanorod, 0.92 μm for ZnO/CoS, 1.30 μm for ZnO/NiS, 0.29 μm for ZnO/CuS, and 0.86 μm for ZnO/PbS, as shown in Fig. 1 below.

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Fig. 1 The film thicknesses for the metal sulfides on ZnO nanorod: (k) ZnO nanorod, (l) ZnO/CoS, (m) ZnO/NiS, (n) ZnO/CuS, and (o) ZnO/PbS.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.